

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

- 5 1. (currently amended) A method for forming a light emitting diode comprising following steps:  
forming a first stack;  
forming a second reaction layer over said first stack;  
forming a second stack;  
10 forming a first reaction layer over said second stack; and  
holding together said first reaction layer and said second reaction layer by means of ~~an organic~~ a transparent adhesive layer;  
wherein the first and second reaction layers each comprise material selected from a group consisting of ~~SiNx, Ti, and Cr and metal~~.
- 15 2. (original) The method of claim 1 wherein the step of forming a first stack comprises following steps:  
providing a first substrate;  
forming a second contact layer on the first substrate;  
20 forming a second cladding layer on the second contact layer;  
forming an emitting layer on the second cladding layer;  
forming a first cladding layer on the emitting layer;  
forming a first contact layer on the first cladding layer; and  
forming a transparent conductive layer on the first contact layer.
- 25 3. (original) The method of claim 2 further comprising following steps:  
removing the first substrate;  
etching the second contact layer, the second cladding layer, the emitting layer,  
first cladding layer, and the first contact layer; and  
30 forming a first electrode on the second contact layer, and a second electrode on  
the transparent conductive layer.

4. (original) The method of claim 2 wherein the first substrate comprises at least one material selected from a group consisting of GaP, GaAs, and Ge.
5. 5. (original) The method of claim 2 wherein the first contact layer and the second contact layer each comprise at least one material selected from a group consisting of GaP, GaAs, GaAsP, InGaP, AlGaInP, and AlGaAs.
10. 6. (original) The method of claim 2 wherein the first cladding layer, the emitting layer, and the second cladding layer each comprise AlGaInP.
15. 7. (original) The method of claim 2 wherein the transparent conductive layer comprises at least one material selected from a group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, zinc tin oxide, BeAu, GeAu, and Ni/Au.
8. (cancelled)
9. 20. (currently amended) The method of claim 1 wherein the ~~organic~~ transparent adhesive layer comprises at least one material selected from a group consisting of PI, BCB, and PFCB.
10. 25. (original) The method of claim 1 wherein forming a second stack comprises forming a second substrate.
11. 11. (original) The method of claim 10 wherein the second substrate comprises at least one material selected from a group consisting of SiC, Al2O3, glass materials, quartz, GaP, GaAsP, and AlGaAs.
30. 12. (currently amended) The method of claim 1 wherein said first reaction layer and said second reaction layer are held together with the ~~organic~~ transparent adhesive layer by chemical bonds.

13. (original) The method of claim 12 wherein the chemical bonds are hydrogen bonds or ionic bonds.

5 14. (cancelled).

15. (new) The method of claim 1 wherein the metal comprises at least one material selected from a group consisting of Ti, and Cr.